

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

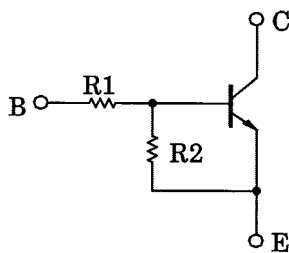
# RN1207, RN1208, RN1209

Switching, Inverter Circuit, Interface Circuit  
And Driver Circuit Applications

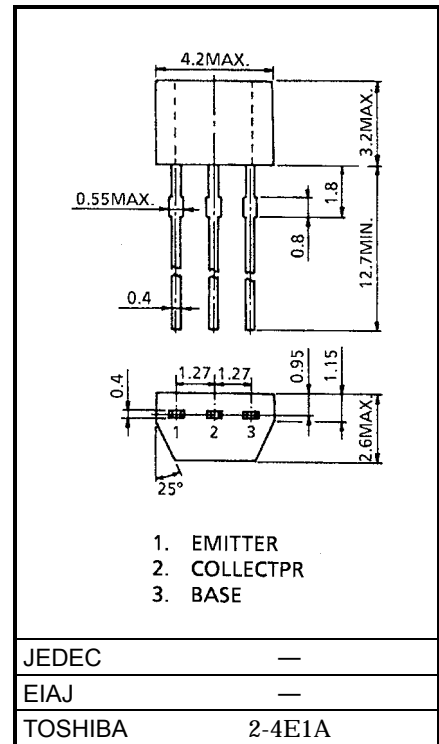
Unit in mm

- With built-in bias resistors.
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2207~2209

## Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2207	10	47
RN2208	22	47
RN2209	47	22



Weight: 0.13g

## Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	RN1207	6
		RN1208	7
		RN1209	15
Collector current	$I_c$	100	mA
Collector power dissipation	$P_c$	300	mW
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55~150	°C

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**Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		$I_{CBO}$	—	$V_{CB} = 50V, I_E = 0$	—	—	100	nA
		$I_{CEO}$	—	$V_{CE} = 50V, I_B = 0$	—	—	500	nA
Emitter cut-off current	RN1207	$I_{EBO}$	—	$V_{EB} = 6V, I_C = 0$	0.081	—	0.15	mA
	RN1208		—	$V_{EB} = 7V, I_C = 0$	0.078	—	0.145	
	RN1209		—	$V_{EB} = 15V, I_C = 0$	0.167	—	0.311	
DC current gain	RN1207	$h_{FE}$	—	$V_{CE} = 5V, I_C = 10mA$	80	—	—	—
	RN1208		—		80	—	—	
	RN1209		—		70	—	—	
Collector-emitter saturation voltage		$V_{CE(sat)}$	—	$I_C = 5mA, I_B = 0.25mA$	—	0.1	0.3	V
Input voltage (ON)	RN1207	$V_{I(ON)}$	—	$V_{CE} = 0.2V, I_C = 5mA$	0.7	—	1.8	V
	RN1208		—		1.0	—	2.6	
	RN1209		—		2.2	—	5.8	
Input voltage (OFF)	RN1207	$V_{I(OFF)}$	—	$V_{CE} = 5V, I_C = 0.1mA$	0.5	—	1.0	V
	RN1208		—		0.6	—	1.16	
	RN1209		—		1.5	—	2.6	
Translation frequency		$f_T$	—	$V_{CE} = 10V, I_C = 5mA$	—	250	—	MHz
Collector output capacitance		$C_{ob}$	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	3	6	pF
Input resistor	RN1207	R1	—	—	7	10	13	kΩ
	RN1208		—		15.4	22	28.6	
	RN1209		—		32.9	47	61.1	
Resistor Ratio	RN1207	R1/R2	—	—	0.191	0.213	0.232	—
	RN1208		—		0.421	0.468	0.515	
	RN1209		—		1.92	2.14	2.35	

